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(54) **Electron emission device**

(57) An electron emission device includes electron emission regions formed on a first substrate, a driving electrode for controlling emission of electrons emitted from the electron emission regions, and a focusing electrode for focusing the electrons and having an opening through which the electrons pass. A first insulating layer is disposed between the driving electrode and the focusing electrode. The focusing electrode and the insulating

layer satisfy at least one of the following two conditions: $1.0 \leq |V_f/t| \leq 6.0$; and $0.2 \leq |V_f/W_h| \leq 0.4$, where V_f (V) indicates the voltage applied to the focusing electrode, t (μm) indicates the thickness of the insulating layer, and W_h (μm) indicates the width of the opening of the focusing electrode.

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